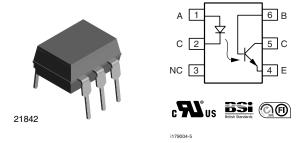
Vishay Semiconductors



Optocoupler, Phototransistor Output, with Base Connection



DESCRIPTION

The 4N25 family is an industry standard single channel phototransistor coupler. This family includes the 4N25, 4N26, 4N27, 4N28. Each optocoupler consists of gallium arsenide infrared LED and a silicon NPN phototransistor.

FEATURES

- Isolation test voltage 5000 V_{RMS}
- Interfaces with common logic families
- Input-output coupling capacitance < 0.5 pF
- Industry standard dual-in-line 6 pin package
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC





APPLICATIONS

- AC mains detection
- · Reed relay driving
- Switch mode power supply feedback
- Telephone ring detection
- · Logic ground isolation
- Logic coupling with high frequency noise rejection

AGENCY APPROVALS

- UL1577, file no. E52744
- BSI: EN 60065:2002, EN 60950:2000
- FIMKO: EN 60950, EN 60065, EN 60335

ORDER INFORMATION				
PART	REMARKS			
4N25	CTR > 20 %, DIP-6			
4N26	CTR > 20 %, DIP-6			
4N27	CTR > 10 %, DIP-6			
4N28	CTR > 10 %, DIP-6			

ABSOLUTE MAXIMUM RATINGS (1)							
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT			
INPUT							
Reverse voltage		V_{R}	5	V			
Forward current		I _F	60	mA			
Surge current	t ≤ 10 µs	I _{FSM}	3	Α			
Power dissipation		P _{diss}	100	mW			
OUTPUT							
Collector emitter breakdown voltage		V _{CEO}	70	V			
Emitter base breakdown voltage		V _{EBO}	7	V			
Collector current		Ic	50	mA			
Collector current	t≤1 ms	Ic	100	mA			
Power dissipation		P _{diss}	150	mW			



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ABSOLUTE MAXIMUM RATINGS (1)							
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT			
COUPLER							
Isolation test voltage		V _{ISO}	5000	V _{RMS}			
Creepage distance			≥ 7	mm			
Clearance distance			≥ 7	mm			
Isolation thickness between emitter and detector			≥ 0.4	mm			
Comparative tracking index	DIN IEC 112/VDE 0303, part 1		175				
	V _{IO} = 500 V, T _{amb} = 25 °C	R _{IO}	10 ¹²	Ω			
Isolation resistance	V _{IO} = 500 V, T _{amb} = 100 °C	R _{IO}	10 ¹¹	Ω			
Storage temperature		T _{stg}	- 55 to + 125	°C			
Operating temperature		T _{amb}	- 55 to + 100	°C			
Junction temperature		Tj	125	°C			
Soldering temperature (2)	max.10 s dip soldering: distance to seating plane ≥ 1.5 mm	T _{sld}	260	°C			

Notes

⁽²⁾ Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering condditions for through hole devices (DIP).

ELECTRICAL CHARACTERISTICS (1)								
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT	
INPUT								
Forward voltage (2)	$I_F = 50 \text{ mA}$		V _F		1.3	1.5	V	
Reverse current (2)	V _R = 3 V		I _R		0.1	100	μΑ	
Capacitance	V _R = 0 V		Co		25		pF	
OUTPUT								
Collector base breakdown voltage (2)	I _C = 100 μA		BV _{CBO}	70			V	
Collector emitter breakdown voltage (2)	I _C = 1 mA		BV _{CEO}	30			V	
Emitter collector breakdown voltage (2)	I _E = 100 μA		BV _{ECO}	7			V	
I _{CEO} (dark) ⁽²⁾	V _{CE} = 10 V, (base open)	4N25			5	50	nA	
		4N26			5	50	nA	
		4N27			5	50	nA	
		4N28			10	100	nA	
I _{CBO} (dark) (2)	V _{CB} = 10 V, (emitter open)				2	20	nA	
Collector emitter capacitance	V _{CE} = 0		C _{CE}		6		pF	
COUPLER								
Isolation test voltage (2)	Peak, 60 Hz		V _{IO}	5000			V	
Saturation voltage, collector emitter	$I_{CE} = 2 \text{ mA}, I_{F} = 50 \text{ mA}$		V _{CE(sat)}			0.5	V	
Resistance, input output (2)	V _{IO} = 500 V		R _{IO}	100			GΩ	
Capacitance, input output	f = 1 MHz		C _{IO}		0.6		pF	

Notes

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

 $^{^{(1)}}$ T_{amb} = 25 °C, unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

 $^{^{(1)}}$ T_{amb} = 25 °C, unless otherwise specified.

⁽²⁾ JEDEC registered values are 2500 V, 1500 V, 1500 V, and 500 V for the 4N25, 4N26, 4N27, and 4N28 respectively.

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CURRENT TRANSFER RATIO (1)								
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT	
DC current transfer ratio	V _{CE} = 10 V, I _F = 10 mA	4N25	CTR _{DC}	20	50		%	
		4N26	CTR _{DC}	20	50		%	
		4N27	CTR _{DC}	10	30		%	
		4N28	CTR _{DC}	10	30		%	

Note

⁽¹⁾ Indicates JEDEC registered values.

SWITCHING CHARACTERISTICS								
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Rise and fall times	V_{CE} = 10 V, I_F = 10 mA, R_L = 100 Ω	t _r , t _f		2		μs		

TYPICAL CHARACTERISTICS

T_{amb} = 25 °C, unless otherwise specified

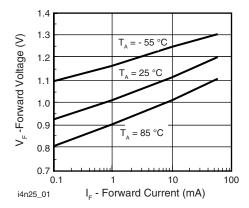


Fig. 1 - Forward Voltage vs. Forward Current

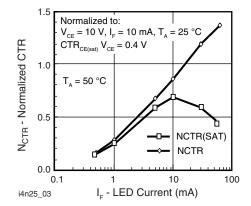


Fig. 3 - Normalized Non-Saturated and Saturated CTR vs. LED Current

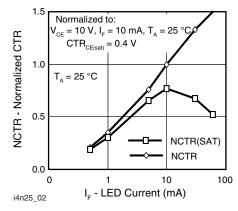


Fig. 2 - Normalized Non-Saturated and Saturated CTR vs. LED Current

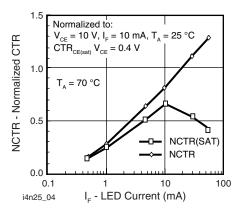


Fig. 4 - Normalized Non-Saturated and Saturated CTR vs. LED Current

= 25 °C



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Normalized to:

 $V_{CB} = 9.3 \text{ V}, I_F = 10 \text{ mA}, T_A$

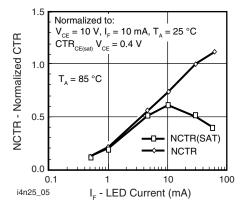


Fig. 5 - Normalized Non-Saturated and Saturated CTR vs. **LED Current**

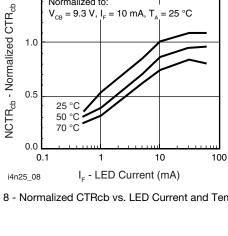


Fig. 8 - Normalized CTRcb vs. LED Current and Temperature

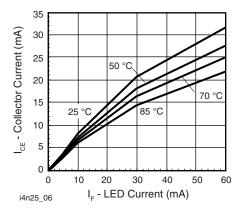


Fig. 6 - Collector Emitter Current vs. Temperature and LED Current

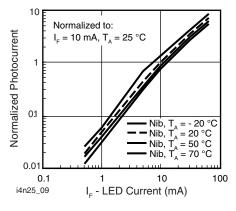


Fig. 9 - Normalized Photocurrent vs. I_F and Temperature

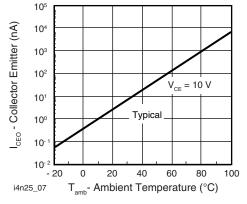


Fig. 7 - Collector Emitter Leakage Current vs. Temperature

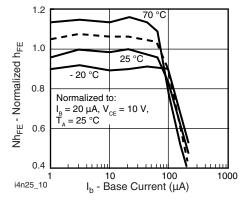


Fig. 10 - Normalized Non-Saturated hFE vs. Base Current and Temperature

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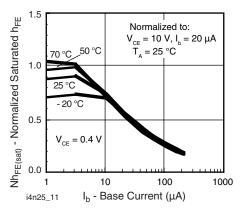


Fig. 11 - Normalized h_{FE} vs. Base Current and Temperature

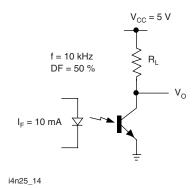


Fig. 14 - Switching Schematic

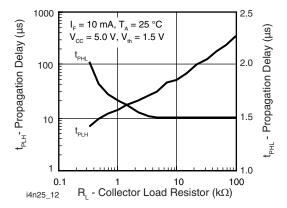


Fig. 12 - Propagation Delay vs. Collector Load Resistor

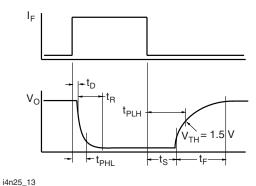
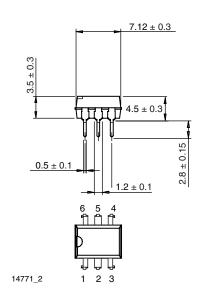


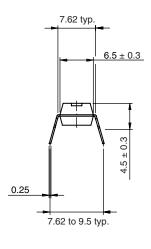
Fig. 13 - Switching Timing



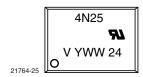
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PACKAGE DIMENSIONS in millimeters





PACKAGE MARKING





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